

Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Low threshold voltage
- Fast switching
- Trench MOSFET technology
- 2 kV ESD protection
- AEC-Q101 qualified

3. Applications

- Relay driver
- High-speed line driver
- High-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _{amb} = 25 °C		-	-	-20	V
V_{GS}	gate-source voltage			-12	-	12	V
I _D	drain current	V_{GS} = -4.5 V; T_{amb} = 25 °C; $t \le 5$ s	[1]	-	-	-4.1	Α
Static characteristics							,
R _{DSon}	drain-source on-state resistance	V_{GS} = -4.5 V; I_D = -2 A; T_j = 25 °C		-	70	85	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	<u> </u>	D I
2	D	drain		
3	G	gate	<u>0</u> 1	G T
4	S	source	TSOP6 (SOT457)	
5	D	drain		
6	D	drain		S 017aaa259

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMN70XPEA	TSOP6	plastic surface-mounted package (TSOP6); 6 leads	SOT457			

7. Marking

Table 4. Marking codes

Type number	Marking code
PMN70XPEA	BB

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _{amb} = 25 °C		-	-20	V
V_{GS}	gate-source voltage			-12	12	V
I _D	drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$	[1]	-	-4.1	Α
		V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-3.2	Α
		V _{GS} = -4.5 V; T _{amb} = 100 °C	[1]	-	-2	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10$ μs		-	-12.8	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	500	mW
			[1]	-	1220	mW
		$T_{sp} = 25 ^{\circ}C$		-	6250	mW
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain	n diode					,
I _S	source current	T _{amb} = 25 °C	[1]	-	-1.3	Α
ESD maximu	um rating					
V _{ESD}	electrostatic discharge voltage	НВМ	[3]	-	2000	V

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm²

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[3] Measured between all pins.

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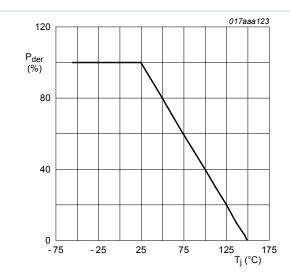


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

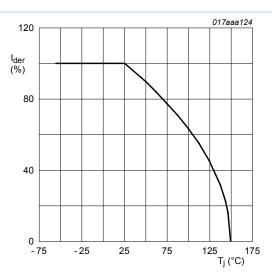


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

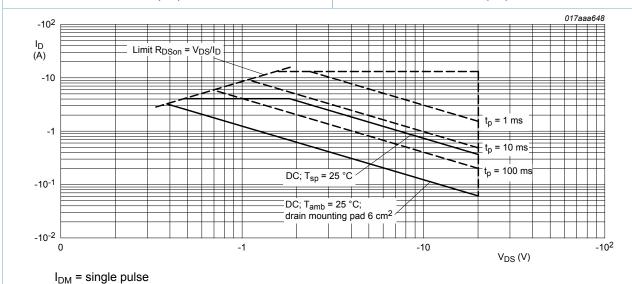


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance	in free air	[1]	-	216	250	K/W
	from junction to		[2]	-	89	102	K/W
ambient		[3]	-	55	63	K/W	

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point		-	15	20	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm²
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm², $t \le 5$ s

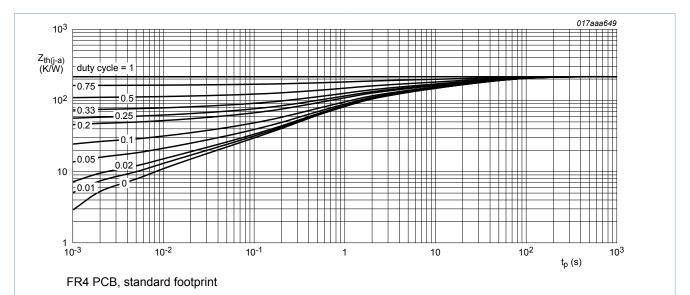
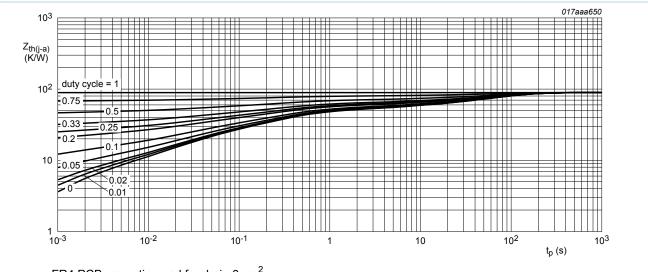


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 6 cm²

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-20	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = -250 \mu A; V_{DS} = V_{GS}; T_j = 25 ^{\circ}C$	-0.75	-1	-1.25	V
I _{DSS}	drain leakage current	V_{DS} = -20 V; V_{GS} = 0 V; T_j = 25 °C	-	-	-1	μΑ
		V _{DS} = -20 V; V _{GS} = 0 V; T _{amb} = 150 °C	-	-	-10	μΑ
I _{GSS}	gate leakage current	V _{GS} = 12 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μA
		V_{GS} = -12 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-10	μΑ
Doon	drain-source on-state	V_{GS} = -4.5 V; I_D = -2 A; T_j = 25 °C	-	70	85	mΩ
	resistance	V _{GS} = -4.5 V; I _D = -2 A; T _j = 150 °C	-	98	118	mΩ
		V_{GS} = -2.5 V; I_D = -1.5 A; T_j = 25 °C	-	101	129	mΩ
9 _{fs}	forward transconductance	V_{DS} = -10 V; I_{D} = -2 A; T_{j} = 25 °C	-	7	-	S
Dynamic cl	naracteristics					
Q _{G(tot)}	total gate charge	V_{DS} = -10 V; I_{D} = -2 A; V_{GS} = -4.5 V;	-	5.2	7.8	nC
Q_{GS}	gate-source charge	$T_j = 25 ^{\circ}\text{C}$	-	1.1	-	nC
Q_{GD}	gate-drain charge		-	1.3	-	nC
C _{iss}	input capacitance	V _{DS} = -10 V; f = 1 MHz; V _{GS} = 0 V;	-	602	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	101	-	pF
C _{rss}	reverse transfer capacitance		-	75	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -10 V; I_{D} = -2 A; V_{GS} = -4.5 V;	-	7	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega$; $T_j = 25 ^{\circ}C$	-	13	-	ns
t _{d(off)}	turn-off delay time		-	40	-	ns
t _f	fall time		-	17	-	ns
Source-dra	in diode		l .	1		J
V _{SD}	source-drain voltage	$I_S = -0.5 \text{ A}; V_{GS} = 0 \text{ V}; T_i = 25 ^{\circ}\text{C}$	-	-0.7	-1.2	V

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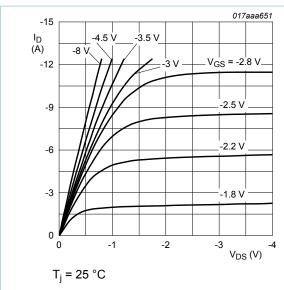
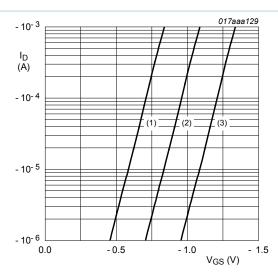


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values



$$T_i$$
 = 25 °C; V_{DS} = -3 V

- (1) minimum values
- (2) typical values
- (3) maximum values

Fig. 7. Sub-threshold drain current as a function of gate-source voltage

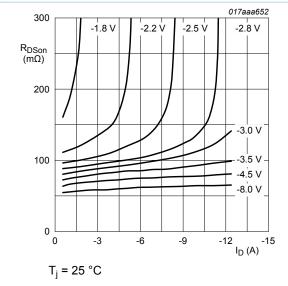


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

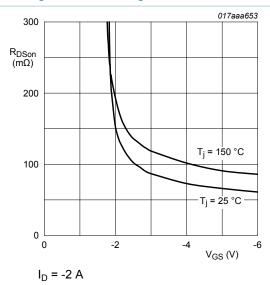


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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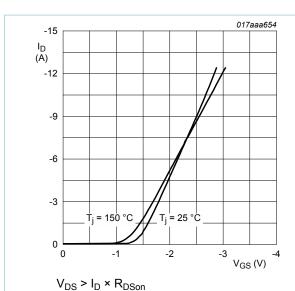


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

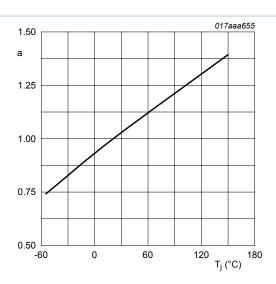


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

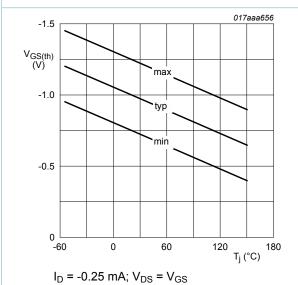


Fig. 12. Gate-source threshold voltage as a function of junction temperature

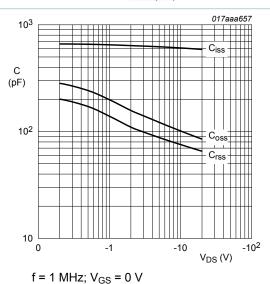


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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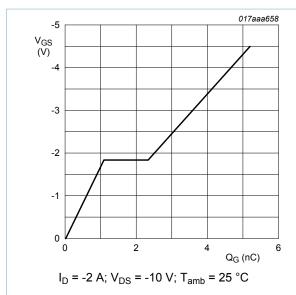


Fig. 14. Gate-source voltage as a function of gate charge; typical values

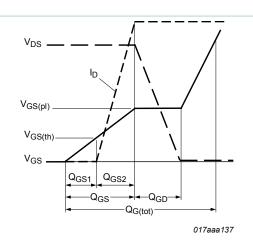


Fig. 15. Gate charge waveform definitions

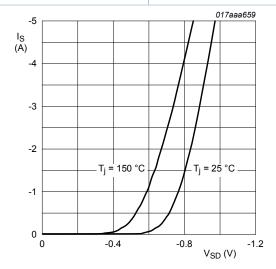
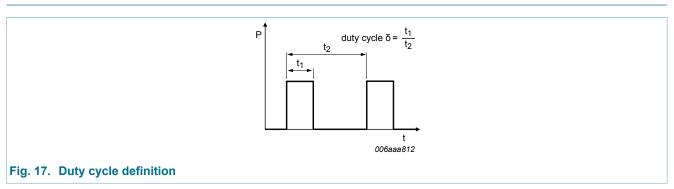


Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

 $V_{GS} = 0 V$



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11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

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12. Package outline

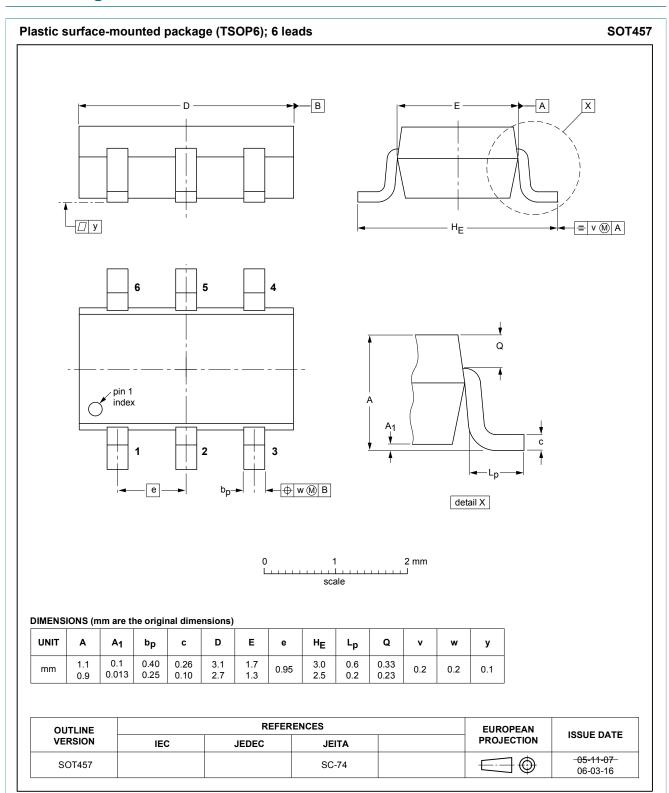


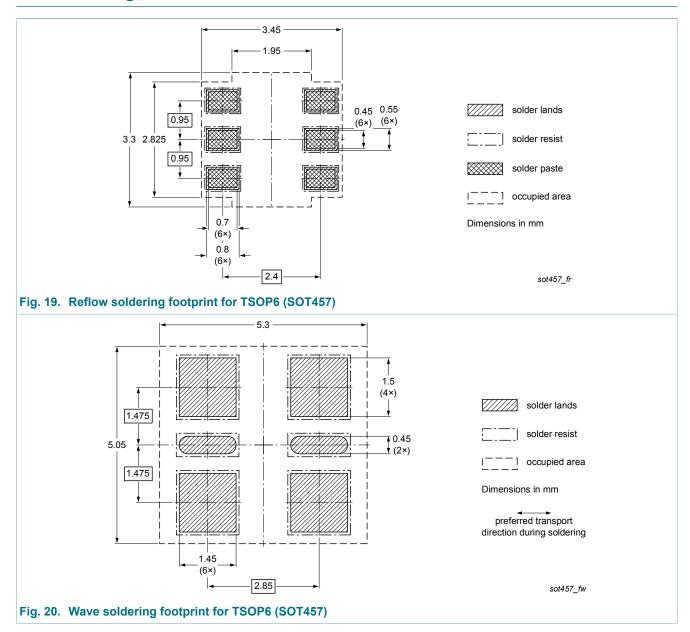
Fig. 18. Package outline TSOP6 (SOT457)

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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMN70XPEA v.1	20140619	Product data sheet	-	-

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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